

Description

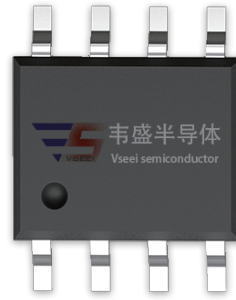
The VSM10N10 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

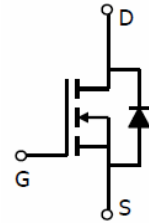
- $V_{DS} = 100V, I_D = 10A$
 $R_{DS(ON)} < 17m\Omega @ V_{GS}=10V$ (Typ:14m Ω)
 $R_{DS(ON)} < 20m\Omega @ V_{GS}=4.5V$ (Typ:15.2m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current

Application

- DC/DC Primary Side Switch
- Telecom/Server
- Synchronous Rectification



SOP-8



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM10N10-S8	VSM10N10	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	10	A
Drain Current-Continuous($T_C=100^{\circ}C$)	$I_D(100^{\circ}C)$	7	A
Pulsed Drain Current	I_{DM}	70	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	40	$^{\circ}C/W$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

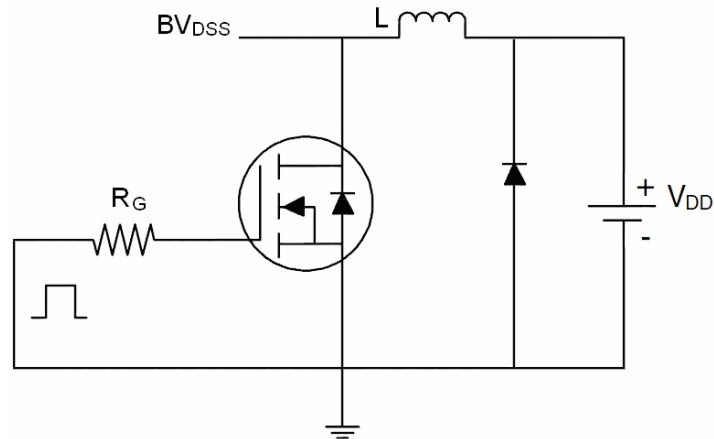
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	110	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.9	1.3	1.8	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	14	17	mΩ
		V _{GS} =4.5V, I _D =10A	-	15.2	20	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =10A	-	26	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	3000	3835	4200	PF
Output Capacitance	C _{OSS}		-	178	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	153	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =10A, R _L =5Ω, R _G =1Ω, V _{GS} =10V	-	13	-	nS
Turn-on Rise Time	t _r		-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	25	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	I _D =10A, V _{DD} =50V, V _{GS} =10V	-	90	-	nC
Gate-Source Charge	Q _{gs}		-	10	-	nC
Gate-Drain Charge	Q _{gd}		-	24	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-	0.85	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	10	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 10A di/dt = 100A/μs ^(Note3)	-	33		nS
Reverse Recovery Charge	Q _{rr}		-	54		nC

Notes:

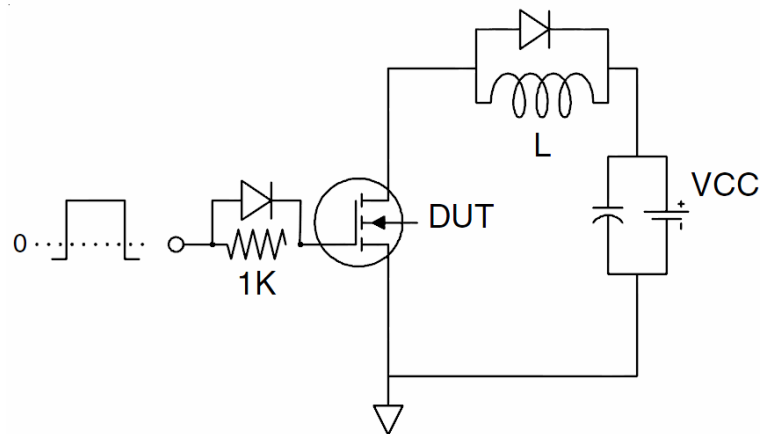
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

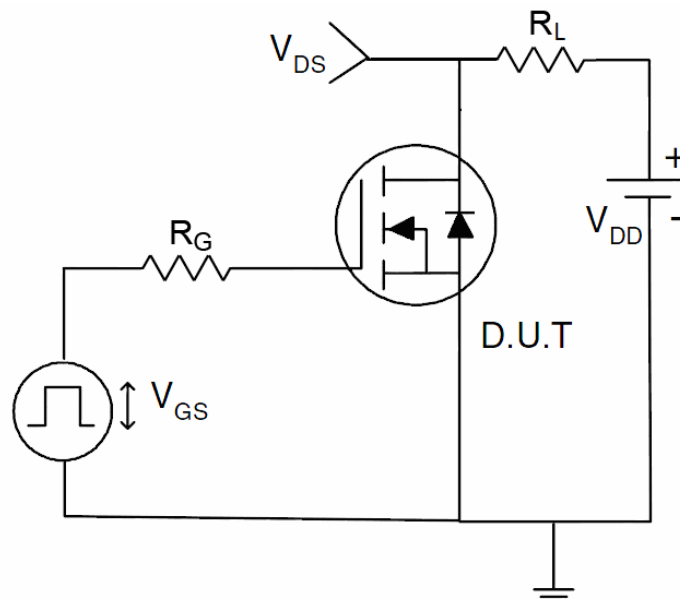
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

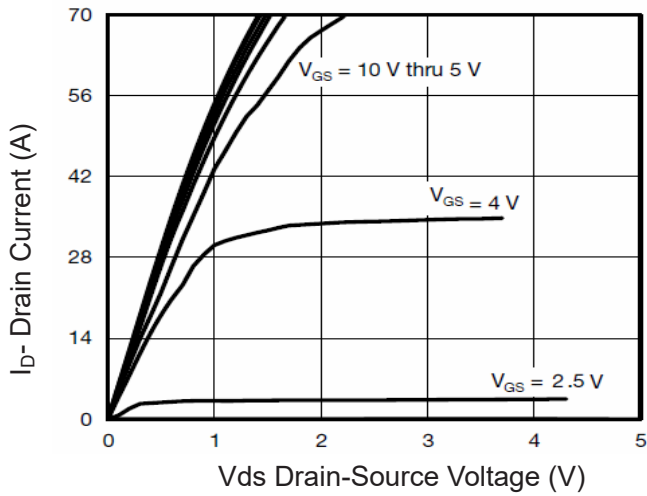


Figure 1 Output Characteristics

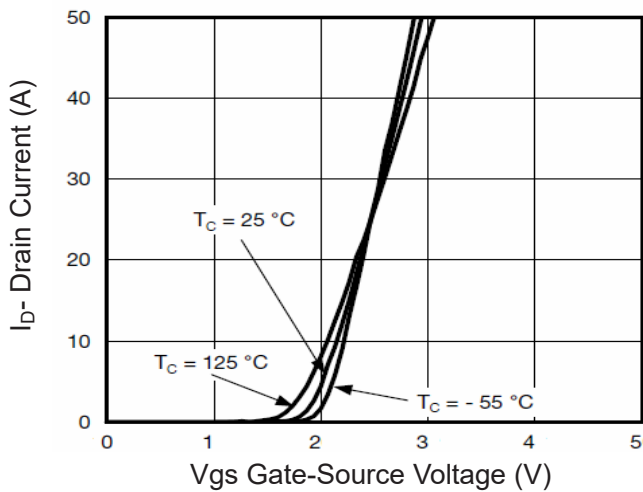


Figure 2 Transfer Characteristics

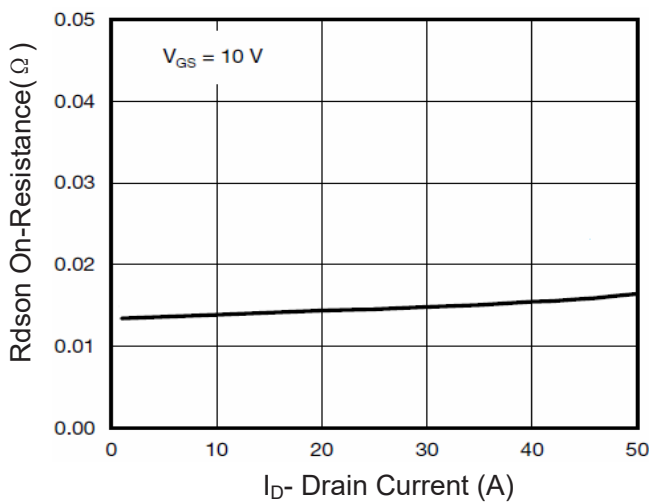


Figure 3 Rdson- Drain Current

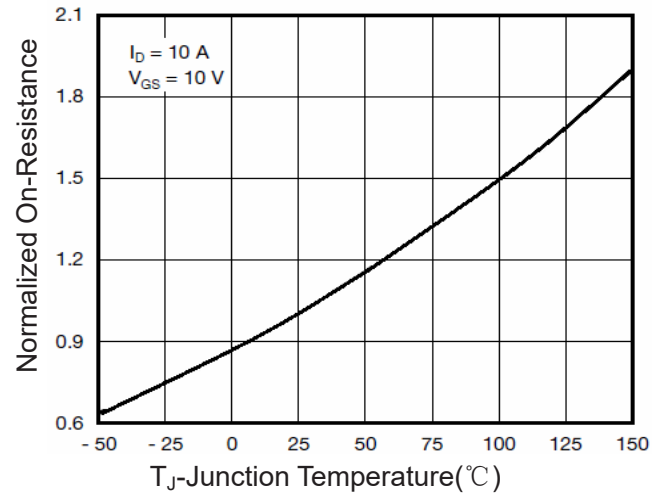


Figure 4 Rdson-Junction Temperature

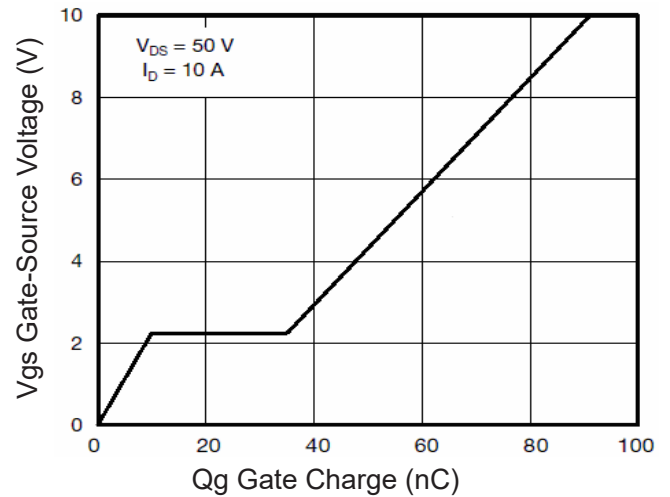


Figure 5 Gate Charge

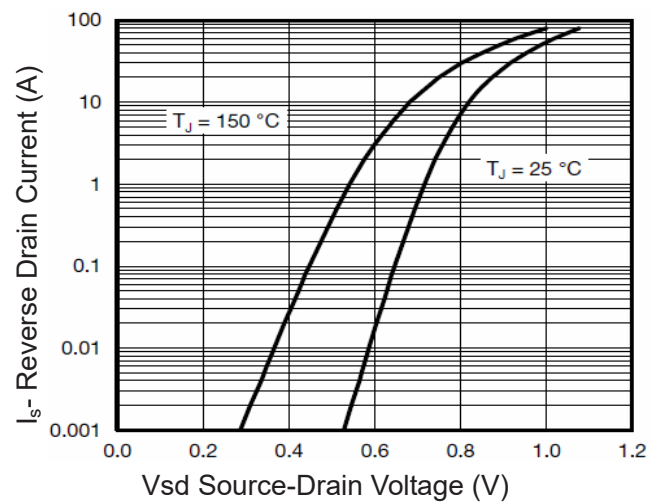
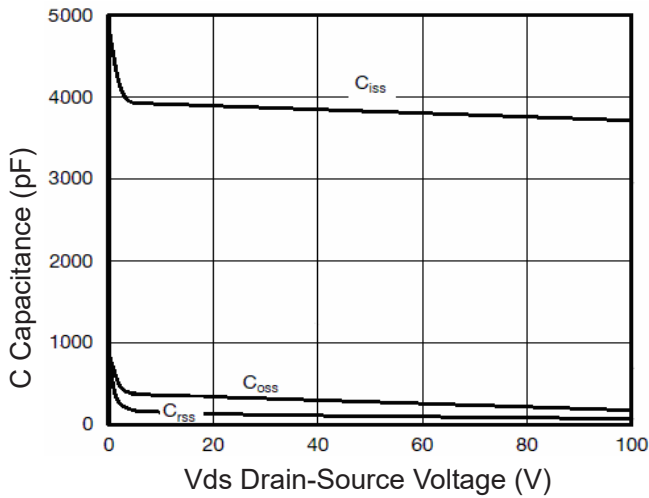
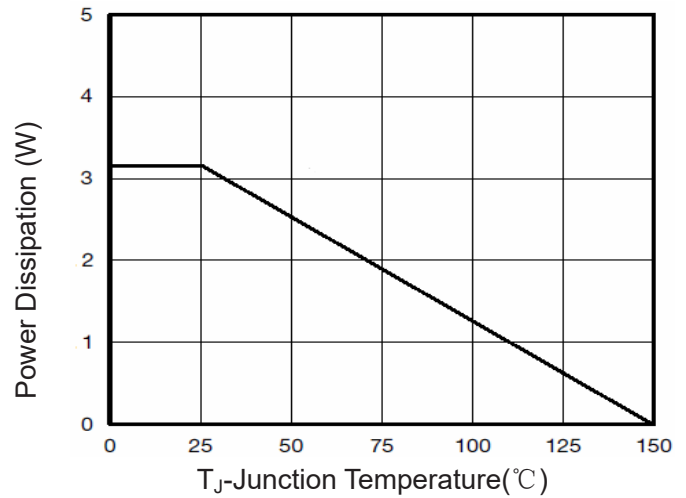
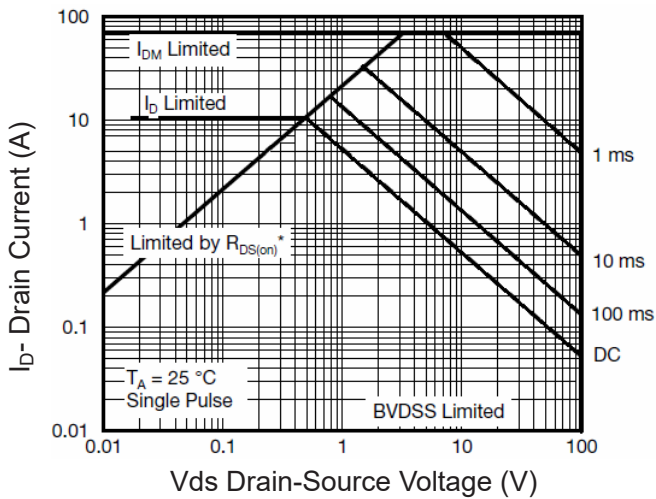
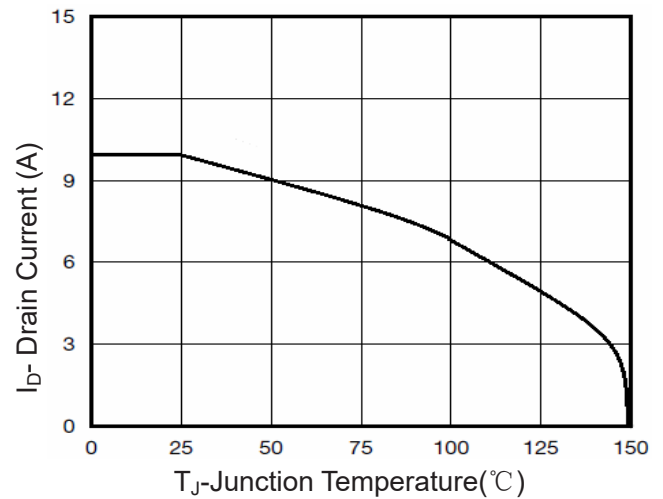
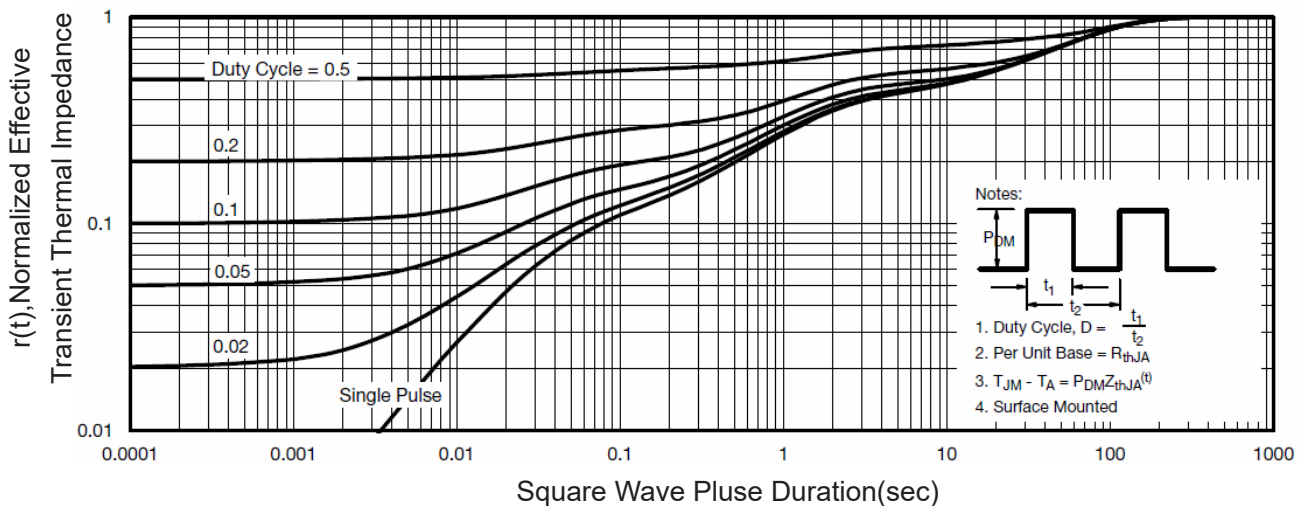


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance